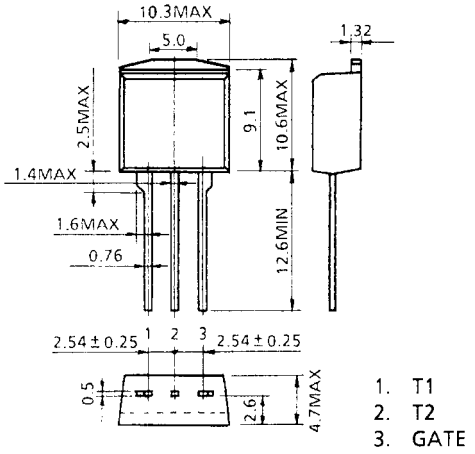
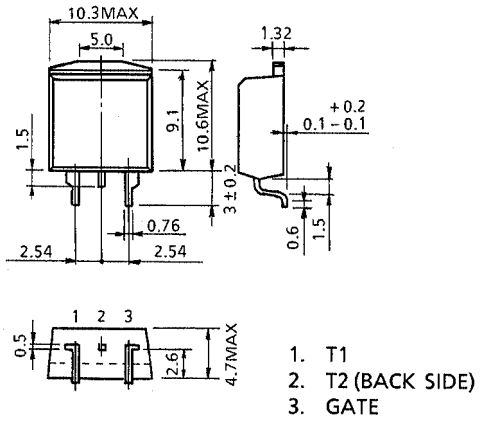
TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12G48,USM12G48,SM12J48,USM12J48 SM12G48A,USM12G48A,SM12J48A,USM12J48A

AC POWER CONTROL APPLICATIONS

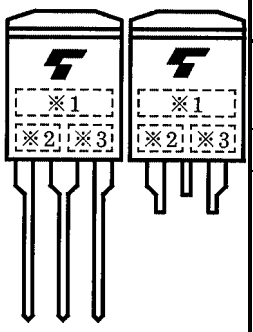
- Repetitive Peak Off-State Voltage : V_{DRM}=400, 600V
- R.M.S. On-State Current : $I_{T\ (RMS)}$ =12A
- Gate Trigger Current : I_{GT}=30mA Max.
  : I_{GT}=20mA Max. ("A"Type)

Unit in mm

SM12G48, SM12J48, SM12G48A, SM12J48A	USM12G48, USM12J48, USM12G48A, USM12J48A
	
JEDEC —	JEDEC —
JEITA —	JEITA —
TOSHIBA 13-10J1A	TOSHIBA 13-10J2A

Weight : 1.7g

MARKING



NUMBER	SYMBOL		MARK
*1	TYPE	SM12G48, SM12G48A, USM12G48, USM12G48A	SM12G48
		SM12J48, SM12J48A, USM12J48, USM12J48A	SM12J48
*2		SM12G48A,SM12J48A,USM12G48A,USM12J48A	A
*3	Lot Number □□ ← Month (Starting from Alphabet A) Year (Last Decimal Digit of the Year of Manufacture)		Example 8A : January 1998 8B : February 1998 8L : December 1998

MAXIMUM RATINGS

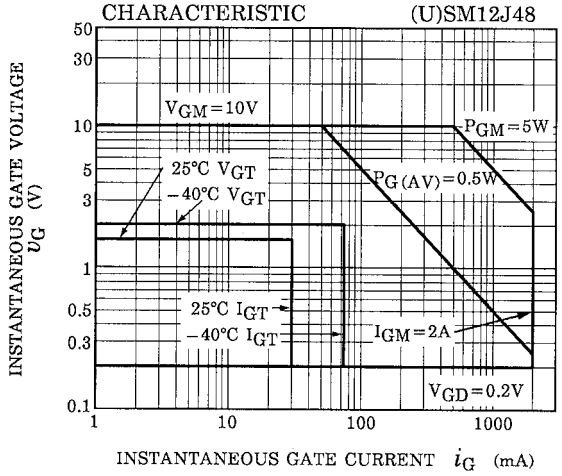
CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	(U)SM12G48 (U)SM12G48A	V_{DRM}	400	V
	(U)SM12J48 (U)SM12J48A		600	
R.M.S On-State Current		$I_{T\ (RMS)}$	12	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	120 (50Hz)	A
			132 (60Hz)	
I^2t Limit Value		I^2t	72	A^2s
Critical Rate of Rise of On-State Current (Note 1)		di /dt	50	A / μs
Peak Gate Power Dissipation		P_{GM}	5	W
Average Gate Power Dissipation		$P_{G\ (AV)}$	0.5	W
Peak Forward Gate Voltage		V_{GM}	10	V
Peak Forward Gate Current		I_{GM}	2	A
Junction Temperature		T_j	−40~125	°C
Storage Temperature Range		T_{stg}	−40~125	°C

Note 1 : V_{DRM}=0.5×Rated
I_{TM}≤15A
t_{gw}≥10μs
t_{gr}≤250ns
i_{gp}=I_{GT}×2.0

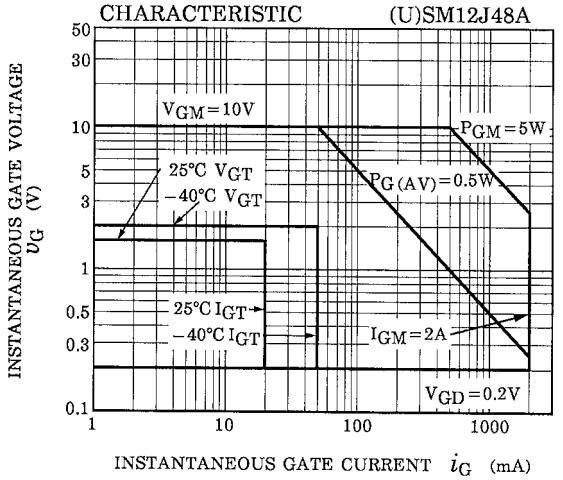
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Repetitive Peak Off-State Current			I_{DRM}	V_{DRM}=Rated		—	—	20	μA
Gate Trigger Voltage		I	V_{GT}	V_D=12V R_L=20Ω	T2 (+) , Gate (+)	—	—	1.5	V
		II			T2 (+) , Gate (−)	—	—	1.5	
		III			T2 (−) , Gate (−)	—	—	1.5	
		IV			T2 (−) , Gate (+)	—	—	—	
Gate Trigger Current	SM12G48 SM12J48	I	I_{GT}	V_D=12V R_L=20Ω	T2 (+) , Gate (+)	—	—	30	mA
		II			T2 (+) , Gate (−)	—	—	30	
		III			T2 (−) , Gate (−)	—	—	30	
		IV			T2 (−) , Gate (+)	—	—	—	
	SM12G48A SM12J48A	I			T2 (+) , Gate (+)	—	—	20	
		II			T2 (+) , Gate (−)	—	—	20	
		III			T2 (−) , Gate (−)	—	—	20	
		IV			T2 (−) , Gate (+)	—	—	—	
Peak On-State Voltage			V_{TM}	I_{TM}=17A		—	—	1.5	V
Gate Non-Trigger Voltage			V_{GD}	V_D=Rated, Tc=125°C		0.2	—	—	V
Holding Current			I_H	V_D=12V, I_{TM}=1A		—	—	50	mA
Thermal Resistance			$R_{th\ (j-c)}$	Junction to Case, AC		—	—	2.4	°C / W
Critical Rate of Rise of Off-State Voltage	(U)SM12G48 (U)SM12J48		dv / dt	V_{DRM}=Rated, T_j=125°C Exponential Rise		—	300	—	V / μs
	(U)SM12G48A (U)SM12J48A					—	200	—	
Critical Rate of Rise of Off-State Voltage at Commutation	(U)SM12G48 (U)SM12J48		(dv / dt) c	V_{DRM}=400V, T_j=125°C (di / dt) c=−6.5A / ms		10	—	—	V / μs
	(U)SM12G48A (U)SM12J48A					4	—	—	

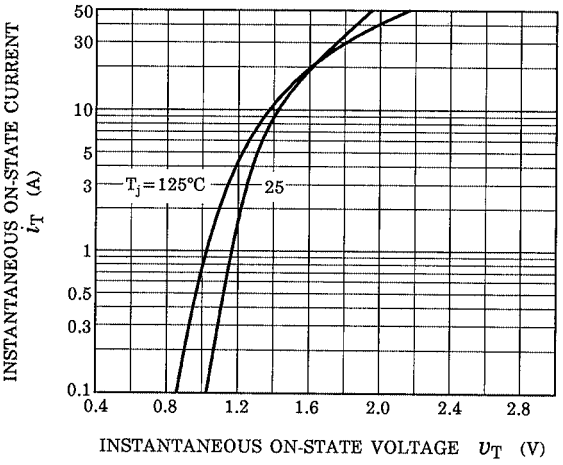
GATE TRIGGER CHARACTERISTIC (U)SM12G48 (U)SM12J48



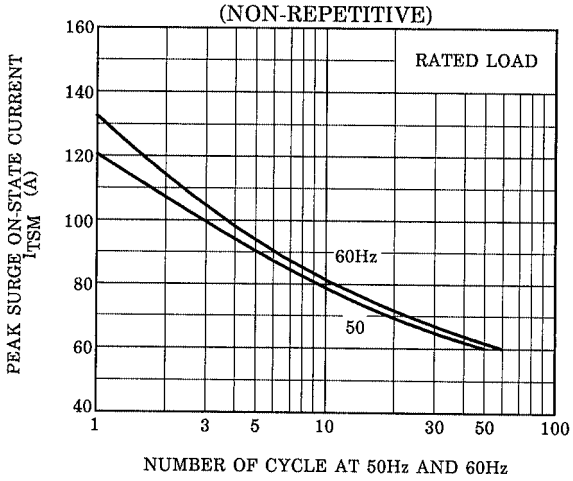
GATE TRIGGER CHARACTERISTIC (U)SM12G48A (U)SM12J48A



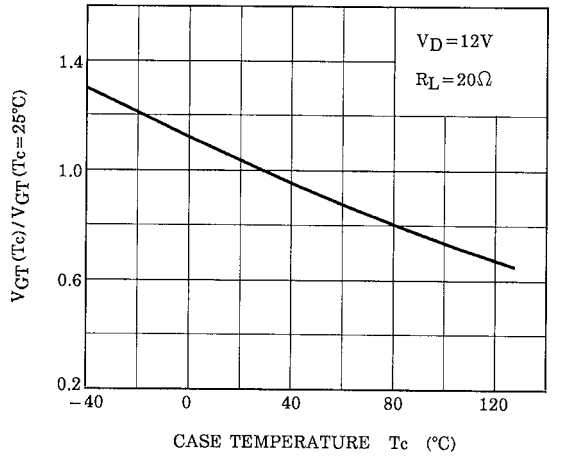
$i_T - v_T$



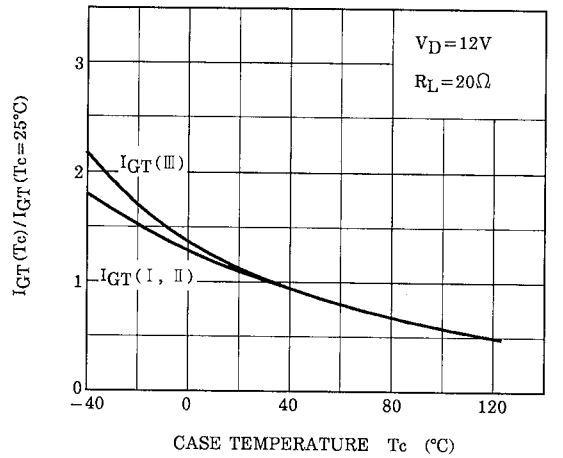
SURGE ON-STATE CURRENT (NON-REPETITIVE)



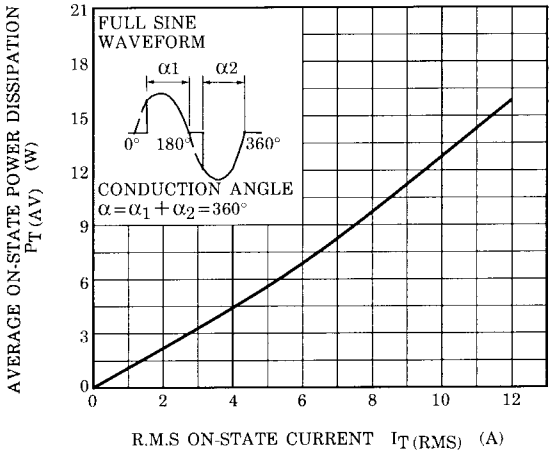
$V_{GT}(Tc) / V_{GT}(Tc=25°C)$ – Tc (TYPICAL)



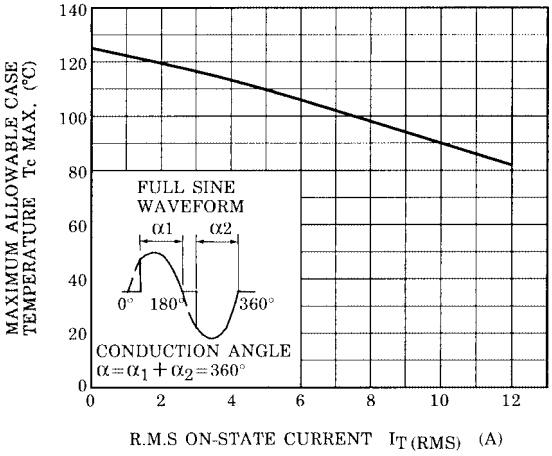
$I_{GT}(Tc) / I_{GT}(Tc=25°C)$ – Tc (TYPICAL)



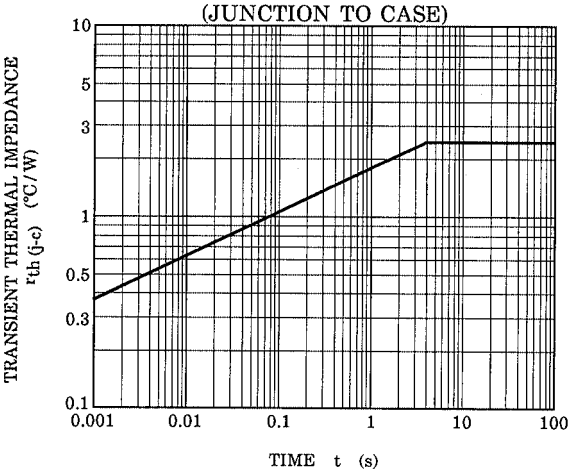
$P_{T(AV)}$ – $I_{T(RMS)}$



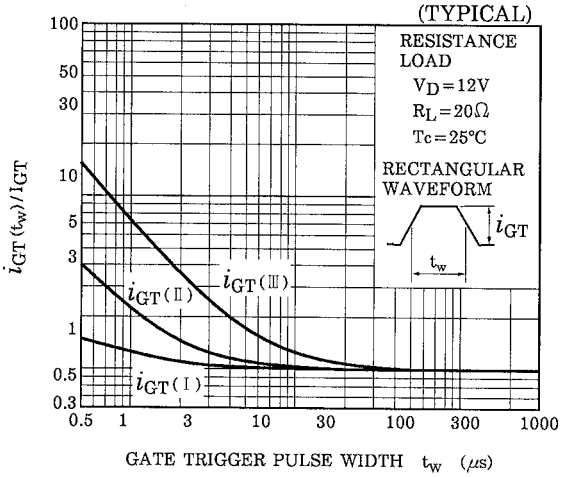
Tc MAX. – $I_{T(RMS)}$



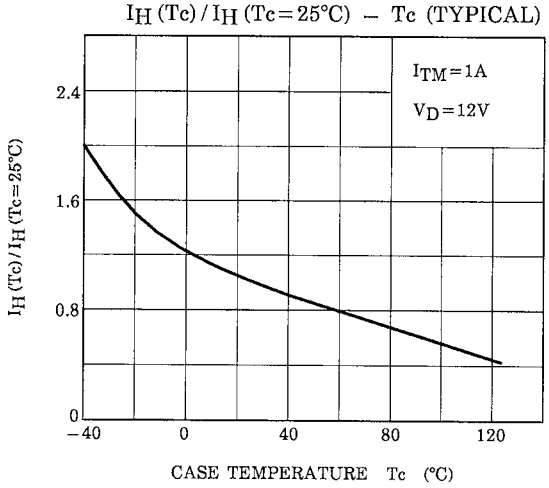
TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



PULSE TRIGGER CHARACTERISTIC (TYPICAL)



I_H (Tc) / I_H (Tc=25°C) – Tc (TYPICAL)



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